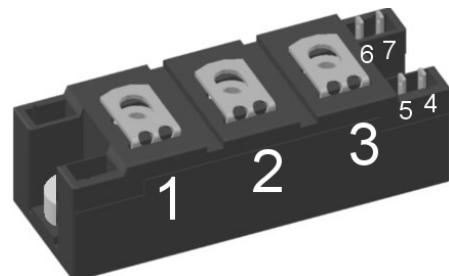


Thyristor Module

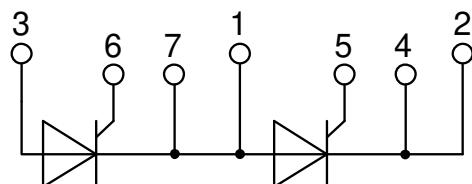
 $V_{RRM} = 2 \times 1800 \text{ V}$
 $I_{TAV} = 200 \text{ A}$
 $V_T = 1.12 \text{ V}$

Phase leg

Part number

MCMA200P1800YA-MI


Backside: isolated

 E72873


Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al2O3-ceramic

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: Y4

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

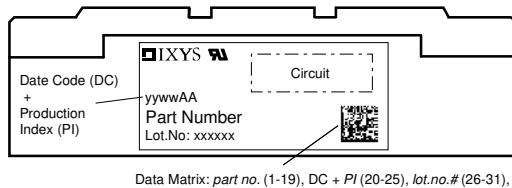
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Thyristor			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^\circ C$			1900	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^\circ C$			1800	V
$I_{R/D}$	reverse current, drain current	$V_{R/D} = 1800 \text{ V}$ $V_{R/D} = 1800 \text{ V}$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 140^\circ C$		300 10	μA mA
V_T	forward voltage drop	$I_T = 200 \text{ A}$ $I_T = 400 \text{ A}$	$T_{VJ} = 25^\circ C$		1.17 1.40	V
		$I_T = 200 \text{ A}$ $I_T = 400 \text{ A}$	$T_{VJ} = 125^\circ C$		1.12 1.41	V
I_{TAV}	average forward current	$T_C = 85^\circ C$	$T_{VJ} = 140^\circ C$		200	A
$I_{T(RMS)}$	RMS forward current	180° sine			315	A
V_{TO} r_T	threshold voltage } slope resistance } for power loss calculation only		$T_{VJ} = 140^\circ C$		0.83 1.43	V $m\Omega$
R_{thJC}	thermal resistance junction to case				0.17	K/W
R_{thCH}	thermal resistance case to heatsink				0.09	K/W
P_{tot}	total power dissipation		$T_C = 25^\circ C$		680	W
I_{TSM}	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$T_{VJ} = 45^\circ C$ $V_R = 0 \text{ V}$		6.00 6.48	kA
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$T_{VJ} = 140^\circ C$ $V_R = 0 \text{ V}$		5.10 5.51	kA
I^2t	value for fusing	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$T_{VJ} = 45^\circ C$ $V_R = 0 \text{ V}$		180.0 174.7	kA^2s
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$T_{VJ} = 140^\circ C$ $V_R = 0 \text{ V}$		130.1 126.3	kA^2s
C_J	junction capacitance	$V_R = 400 \text{ V}$ $f = 1 \text{ MHz}$	$T_{VJ} = 25^\circ C$		273	pF
P_{GM}	max. gate power dissipation	$t_p = 30 \mu s$ $t_p = 500 \mu s$	$T_C = 140^\circ C$		120 60 8	W
P_{GAV}	average gate power dissipation					
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 140^\circ C; f = 50 \text{ Hz}$ repetitive, $I_T = 600 \text{ A}$ $t_p = 200 \mu s; di_G/dt = 0.5 \text{ A}/\mu s;$ $I_G = 0.5 \text{ A}; V = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 200 \text{ A}$			100	$\text{A}/\mu s$
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$ $R_{GK} = \infty$; method 1 (linear voltage rise)	$T_{VJ} = 140^\circ C$		1000	$\text{V}/\mu s$
V_{GT}	gate trigger voltage	$V_D = 6 \text{ V}$	$T_{VJ} = 25^\circ C$ $T_{VJ} = -40^\circ C$		2.5 2.6	V
I_{GT}	gate trigger current	$V_D = 6 \text{ V}$	$T_{VJ} = 25^\circ C$ $T_{VJ} = -40^\circ C$		150 200	mA
V_{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 140^\circ C$		0.2	V
I_{GD}	gate non-trigger current				10	mA
I_L	latching current	$t_p = 30 \mu s$ $I_G = 0.5 \text{ A}; di_G/dt = 0.5 \text{ A}/\mu s$	$T_{VJ} = 25^\circ C$		300	mA
I_H	holding current	$V_D = 6 \text{ V}$ $R_{GK} = \infty$	$T_{VJ} = 25^\circ C$		200	mA
t_{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$ $I_G = 0.5 \text{ A}; di_G/dt = 0.5 \text{ A}/\mu s$	$T_{VJ} = 25^\circ C$		2	μs
t_q	turn-off time	$V_R = 100 \text{ V}; I_T = 200 \text{ A}; V = \frac{2}{3} V_{DRM}$ $T_{VJ} = 125^\circ C$ $di/dt = 10 \text{ A}/\mu s$ $dv/dt = 20 \text{ V}/\mu s$ $t_p = 200 \mu s$		150		μs

Package Y4

Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	
I_{RMS}	RMS current	per terminal			300	A
T_{VJ}	virtual junction temperature		-40		140	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		125	°C
Weight				150		g
M_D	mounting torque		2.25		2.75	Nm
M_T	terminal torque		4.5		5.5	Nm
$d_{Spp/App}$	creepage distance on surface / striking distance through air	terminal to terminal	14.0	10.0		mm
$d_{Spb/Apb}$		terminal to backside	16.0	16.0		mm
V_{ISOL}	isolation voltage	t = 1 second t = 1 minute	3600 50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	3000		V V



Data Matrix: part no. (1-19), DC + PI (20-25), lot.no.# (26-31), blank (32), serial no.#(33-36)

Part description

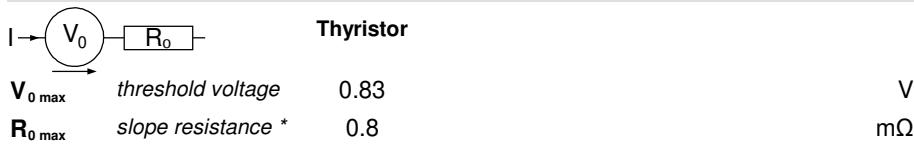
M = Module
 C = Thyristor (SCR)
 M = Thyristor
 A = (up to 1800V)
 200 = Current Rating [A]
 P = Phase leg
 1800 = Reverse Voltage [V]
 YA = Y4-M6
 - = Hyphen
 MI = with metal inserts

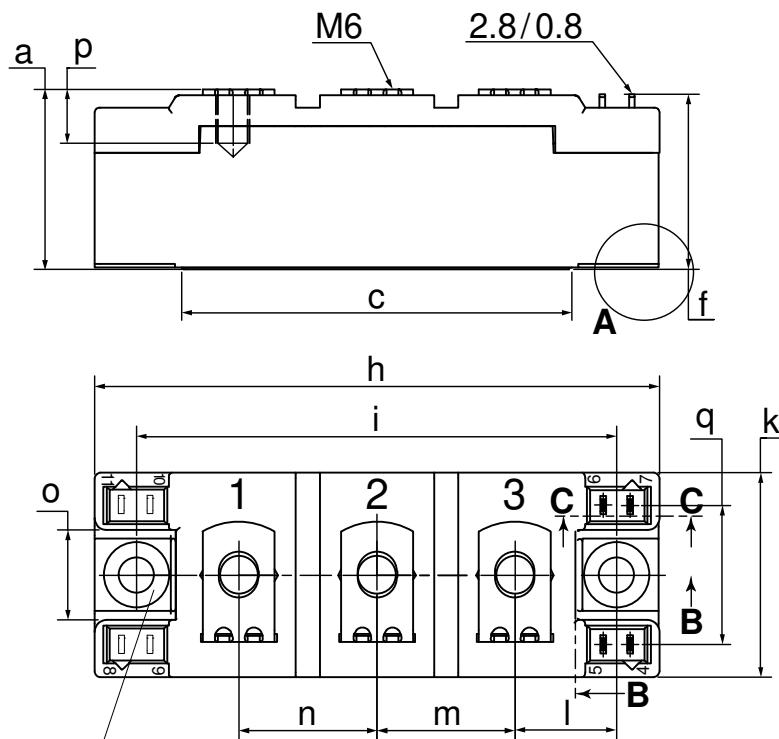
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCMA200P1800YA-MI	MCMA200P1800YA-MI	Box	6	524802

Equivalent Circuits for Simulation

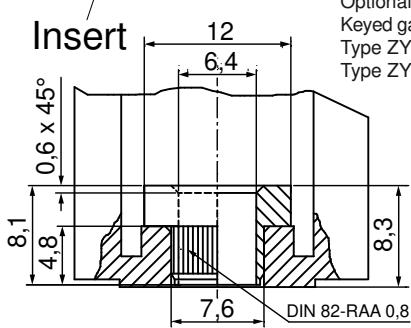
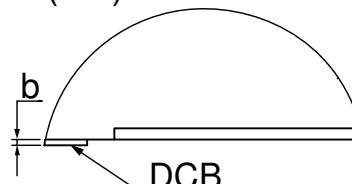
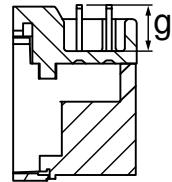
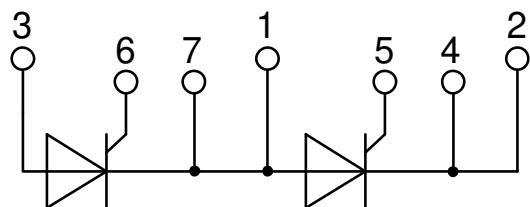
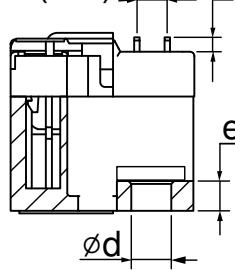
* on die level

$T_{VJ} = 140$ °C



Outlines Y4


Dim.	MIN [mm]	MAX [mm]	MIN [inch]	MAX [inch]
a	30.0	30.6	1.181	1.205
b	typ. 0.25		typ. 0.010	
c	64.0	65.0	2.520	2.559
d	typ. 6.4		typ. 0.250	
e	4.9	5.1	0.193	0.201
f	28.6	29.2	1.126	1.150
g	7.3	7.7	0.287	0.303
h	93.5	94.5	3.681	3.720
i	79.5	80.5	3.130	3.169
j	4.8	5.2	0.189	0.205
k	33.4	34.0	1.315	1.339
l	16.7	17.3	0.657	0.681
m	22.7	23.3	0.894	0.917
n	22.7	23.3	0.894	0.917
o	14.0	15.0	0.551	0.591
p	typ. 10.5		typ. 0.413	
q	22.8	23.3	0.898	0.917
r	1.8	2.4	0.071	0.041


A (3:1)

C-C (1:1)

B-B (1:1)


Thyristor

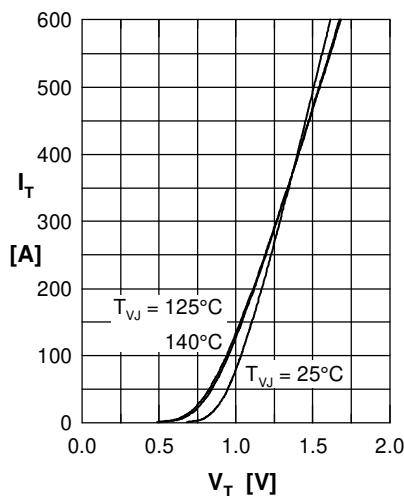


Fig. 1 Forward current vs.
voltage drop per thyristor

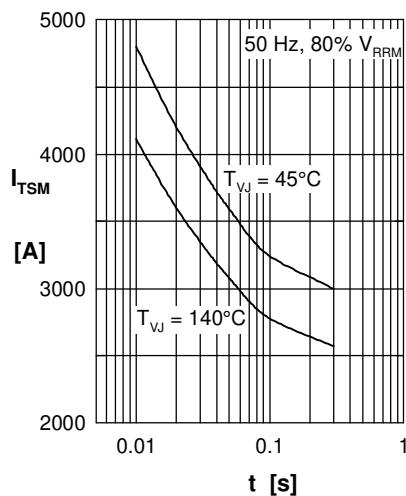


Fig. 2 Surge overload current
vs. time per thyristor

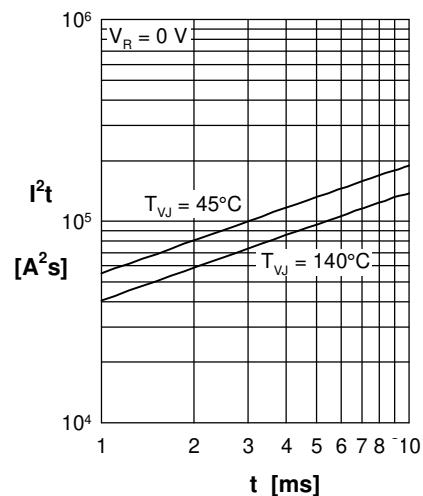


Fig. 3 I^2t vs. time per thyristor

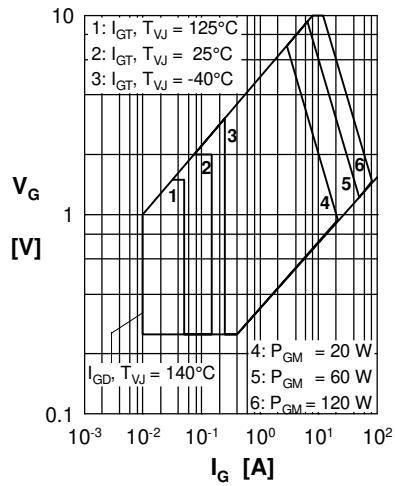


Fig. 4 Gate voltage & gate current

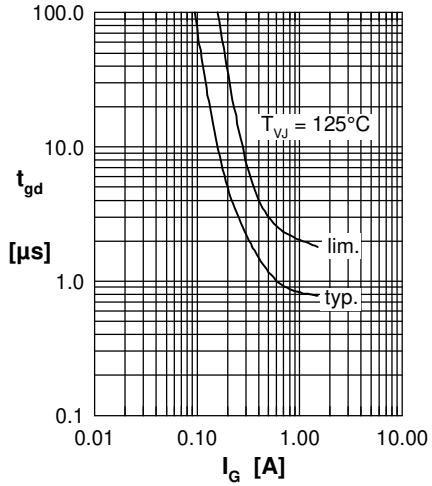


Fig. 5 Gate controlled delay time t_{gd}

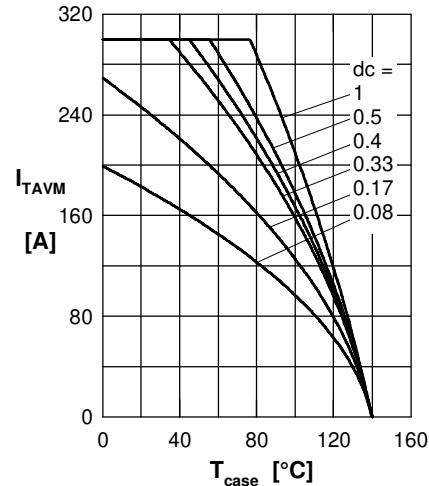


Fig. 6 Max. forward current vs.
case temperature per thy.

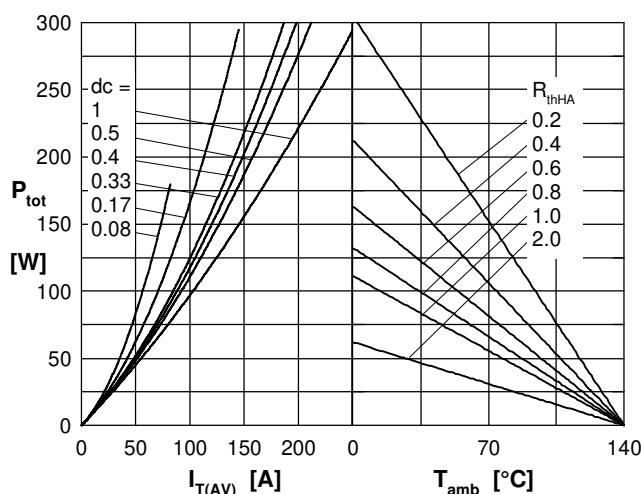


Fig. 7 Power dissipation vs. forward current
and ambient temperature per thyristor

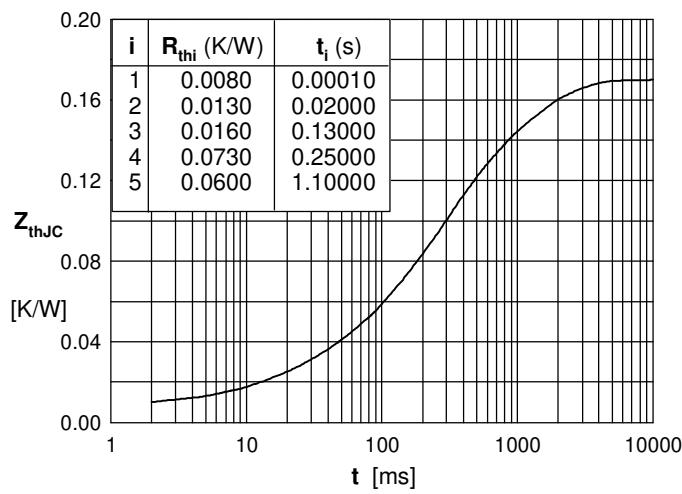


Fig. 8 Transient thermal impedance junction to case
vs. time per thyristor

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